

Water-Induced Nanometer-Thin Crystalline Indium-Praseodymium Oxide Channel Layers for Thin-Film Transistors

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Table S1 Recent advances of solution-processed oxide TFTs based on Si/SiO₂ substrate.

Channel	Mobility (cm ² V ⁻¹ s ⁻¹)	Year	Reference
In-Al-O	0.21	2013	1
In-La-Zn-O	1.81	2013	2
In-Y-Zn-O	2.37	2013	2
In-Sc-Zn-O	2.57	2013	2
In-Zn-O	13.0	2014	3
In-S-Zn-O	8.1	2014	3
In-P-Zn-O	6.3	2014	3
In-Ga-Zn-O	6.8	2015	4
In-B-Zn-O	10.15	2016	5
In-Sb-O	4.6	2017	6
In-Mg-O	13.7	2017	7
In-B-O	11.3	2018	8
In-Ga-Cd-O	10	2018	9
In-Ga-O	0.5	2018	10
In-Y-O	0.4	2018	10
In-Mg-Zn-O	1.97	2019	11
In-Si-O	0.21	2019	12
In-Ni-O	17.71	2019	13
In-Dy-O	7.60	2020	14
Sn-Ga-O	4.26	2020	15
Sn-Li-O	2	2021	16
In-Ga-Sn-O	2.13	2021	17
In-Pr-O	17.03	2022	This work

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